Supporting Information

Ideal two-dimensional nodal-ring semimetal in tetragonal borophene oxide

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Figure S1. The procedure to acquire T-borophene oxide, *i.e.* t-B₂O, from T-borophene.



Figure S2. The phonon dispersion of free-standing T-borophene.

Supporting note: the discussion of formation energy and the realizability of t-B₂O on metal substrates

we calculated the formation energy of t-B₂O with formula $\Delta E = \frac{E(B_x O_y) - xE(B) - yE(O)}{x + y}$, where $E(B_x O_y)$ is the total energy of the material $B_x O_y$, and E(B) and E(O) are the energies per atom in the solid boron α -B₁₂ and oxygen molecule respectively. In combination with the value of ΔE in B₂O₃, which is the most stable bulk boron oxide in Material Project¹, we construct a simple energy convex hull for boron oxide (see Figure S3).



Figure S3. Convex hull for $B_{1-x}O_x$. The convex hull as defined by the bulk phases is represented by the black dashed lines. The blue square denotes the formation energy of t-B₂O.

Despite for a material to be thermodynamically stable requires that ΔE be negative not only relative to its pure elemental phases but relative to all other competing phases, *i.e.* its energy must be below the convex hull. However, this rule in general, but for 2D materials in particular, cannot be directly applied as a criterion for stability and realizability. The most important reasons for this are: (i) the intrinsic uncertainty on the DFT energies stemming from the approximate *xc*-functional in that the accuracy of the PBE functional for the formation energy is only around 0.2 eV per atom on average²; (ii) substrate interactions or other external effects that can stabilize the monolayer, which can be exemplified by lots of 2D materials have been fabricated on different substrates³, such as silicene can be grown on the silver substrate despite its formation energy is 0.66 eV higher than its ground state bulk silicon⁴ or hexagonal borophene has been realized on Aluminum surface⁵ albeit it has high energy and shows huge imaginary frequencies in its phonon dispersion; (iii) kinetic barriers that separate the monolayer from other lower energy phases, as manifested by many metastable 2D graphene allotropes (*e.g.* graphyne family) have been experimentally reported even their formation energy are much higher than that of graphene⁶⁻⁸.



Figure S4. The route to prepare t-B₂O through oxidizing the T-borophene

Substrates, most of the time, play non-negligible roles in stabilizations and fabrications of 2D materials. Up to now, a great deal of 2D materials have been realized on different kinds of substrates, such as silicene/borophene on Ag (111) surface^{5, 9-11}, CuSe on Cu (111)¹², stanene on Bi₂Te₃(111)¹³ or InSb (111)¹⁴, just name a few. Although there are many factors to affect the growth of 2D materials on substrates and it is also not easy to choose a proper substrate to fabricate an ideal 2D material, but

some prerequisites still are considered at first, such as a 2D material usually tends to form more uniform sheets on a symmetry matched surface with small lattice mismatch¹⁵. Based on these considerations, here we attempt to propose a route to realize t-B₂O. We notice that T-borophene has square lattice symmetry with optimized lattice constant a = 4.023 Å and many metals have cubic unit cells with lattice constants very close to that of T-borophene, for example, a = 4.086/4.049/4.078/ Å for Ag/Al/Au. Therefore, T-borophene can be initially grown on the (001) surface of those metals, e.g. Ag(001), then t-B₂O can be obtained through oxidizing as-prepared T-borophene (see Figure S4).



Figure S5. The band structures of t- B_2O at PBE and HSE levels. The comparison between HSE and PBE results didn't show any qualitative change, just the energy window of the nodal-loop has been shifted slightly.



Figure S6. The strain-stress relationship of t-B₂O under uniaxial and biaxial strains.



Figure S7. The calculated phonon spectra of t-B₂O under uniaxial 2% and biaxial 2% strains.

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